

NLAS5223B, NLAS5223BL

Analog Switch, Dual SPDT, Ultra Low 0.35 Ω

The NLAS5223B is an advanced CMOS analog switch fabricated in Sub-micron silicon gate CMOS technology. The device is a dual Independent Single Pole Double Throw (SPDT) switch featuring Ultra-Low R_{ON} of 0.35 Ω , at $V_{CC} = 4.3$ V.

The part also features guaranteed Break Before Make (BBM) switching, assuring the switches never short the driver.

Features

- Ultra-Low R_{ON} , 0.35 Ω (typ) at $V_{CC} = 4.3$ V
- NLAS5223B Interfaces with 2.8 V Chipset
- NLAS5223BL Interfaces with 1.8 V Chipset
- Single Supply Operation from 1.65–4.5 V
- Full 0– V_{CC} Signal Handling Capability
- High Off-Channel Isolation
- Low Standby Current, < 50 nA
- Low Distortion
- R_{ON} Flatness of 0.15 Ω
- High Continuous Current Capability
 - ♦ ± 320 mA Through Each Switch
- Large Current Clamping Diodes at Analog Inputs
 - ♦ ± 100 mA Continuous Current Capability
- Package:
 - ♦ 1.4 x 1.8 x 0.75 mm WQFN10 Pb-Free
 - ♦ 1.4 x 1.8 x 0.55 mm UQFN10 Pb-Free
- These are Pb-Free Devices

Applications

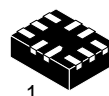
- Cell Phone Audio Block
- Speaker and Earphone Switching
- Ring-Tone Chip/Amplifier Switching
- Modems



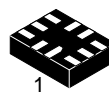
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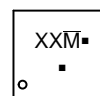
MARKING DIAGRAM



**WQFN10
CASE 488AQ**

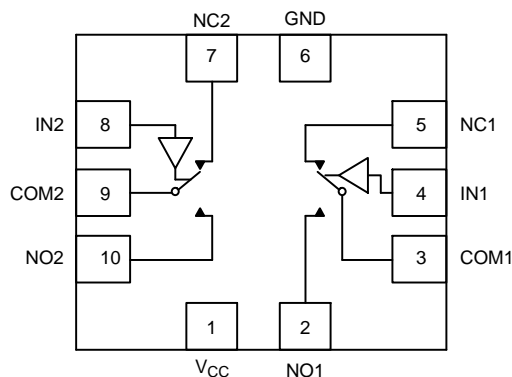


**UQFN10
CASE 488AT**



XX = Specific Device Code
 AD = NLAS5223BMNR2G
 AE = NLAS5223BLMNR2G
 AP = NLAS5223BMUR2G
 M̄ = Date Code/Assembly Location
 ■ = Pb-Free Device

(Note: Microdot may be in either location)



FUNCTION TABLE

| IN 1, 2 | NO 1, 2 | NC 1, 2 |
|---------|---------|---------|
| 0 | OFF | ON |
| 1 | ON | OFF |

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

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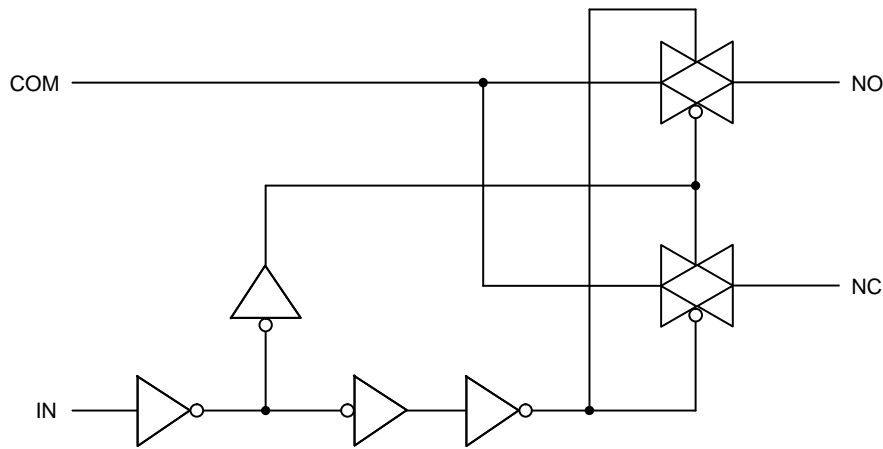


Figure 1. Logic Equivalent Circuit

PIN DESCRIPTION

| QFN PIN # | Symbol | Name and Function |
|-------------|------------------------|-------------------------|
| 2, 5, 7, 10 | NC1 to NC2, NO1 to NO2 | Independent Channels |
| 4, 8 | IN1 and IN2 | Controls |
| 3, 9 | COM1 and COM2 | Common Channels |
| 6 | GND | Ground (V) |
| 1 | V _{CC} | Positive Supply Voltage |

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|----------------------|--|--|------|
| V _{CC} | Positive DC Supply Voltage | -0.5 to +5.5 | V |
| V _{IS} | Analog Input Voltage (V _{NO} , V _{NC} , or V _{COM}) | -0.5 ≤ V _{IS} ≤ V _{CC} + 0.5 | V |
| V _{IN} | Digital Select Input Voltage | -0.5 ≤ V _{IN} ≤ +5.5 | V |
| I _{anl1} | Continuous DC Current from COM to NC/NO | ±320 | mA |
| I _{anl-pk1} | Peak Current from COM to NC/NO, 10% Duty Cycle, 100 ms = t _{ON} (Note 1) | ±600 | mA |
| I _{anl-pk2} | Instantaneous Peak Current from COM to NC/NO, 10% Duty Cycle, t _{ON} < 1 μs | ±850 | mA |
| I _{clmp} | Continuous DC Current into COM/NO/NC with Respect to V _{CC} or GND | ±100 | mA |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Defined as 10% ON, 90% OFF Duty Cycle.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
|---------------------------------|---|------|-----------------|------|
| V _{CC} | DC Supply Voltage | 1.65 | 4.5 | V |
| V _{IN} | Digital Select Input Voltage (OVT) Overvoltage Tolerance | GND | 4.5 | V |
| V _{IS} | Analog Input Voltage (NC, NO, COM) | GND | V _{CC} | V |
| T _A | Operating Temperature Range | -40 | +85 | °C |
| t _r , t _f | Input Rise or Fall Time, SELECT V _{CC} = 1.6 V – 2.7 V V _{CC} = 3.0 V – 4.5 V | | 20 10 | ns/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

NLAS5223B, NLAS5223BL

NLAS5223B DC CHARACTERISTICS – DIGITAL SECTION (Voltages Referenced to GND)

| Symbol | Parameter | Condition | V _{CC} | Guaranteed Limit | | Unit |
|------------------|---|---|-----------------|------------------|----------------|------|
| | | | | 25°C | -40°C to +85°C | |
| V _{IH} | Minimum High-Level Input Voltage, Select Inputs | | 3.0 4.3 | 1.4 2.0 | 1.4 2.0 | V |
| V _{IL} | Maximum Low-Level Input Voltage, Select Inputs | | 3.0 4.3 | 0.7 0.8 | 0.7 0.8 | V |
| I _{IN} | Maximum Input Leakage Current, Select Inputs | V _{IN} = V _{CC} or GND | 4.3 | ±0.1 | ±1.0 | μA |
| I _{OFF} | Power Off Leakage Current | V _{IN} = V _{CC} or GND | 0 | ±0.5 | ±2.0 | μA |
| I _{CC} | Maximum Quiescent Supply Current (Note 2) | Select and V _{IS} = V _{CC} or GND | 1.65 to 4.5 | ±1.0 | ±2.0 | μA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.

NLAS5223B DC ELECTRICAL CHARACTERISTICS – ANALOG SECTION

| Symbol | Parameter | Condition | V _{CC} | Guaranteed Maximum Limit | | | | Unit |
|--|--|--|-----------------|--------------------------|--------------|----------------|--------------|------|
| | | | | 25°C | | -40°C to +85°C | | |
| | | | | Min | Max | Min | Max | |
| R _{ON} | NC/NO On-Resistance (Note 3) | V _{IN} = V _{IL} or V _{IN} = V _{IH} V _{IS} = GND to V _{CC} I _{COM} = 100 mA | 3.0 4.3 | | 0.4 0.35 | | 0.5 0.4 | Ω |
| R _{FLAT} | NC/NO On-Resistance Flatness (Notes 3 and 4) | I _{COM} = 100 mA V _{IS} = 0 to V _{CC} | 3.0 4.3 | | 0.16 0.11 | | 0.20 0.14 | Ω |
| ΔR _{ON} | On-Resistance Match Between Channels (Notes 3 and 5) | V _{IS} = 1.5 V; I _{COM} = 100 mA V _{IS} = 2.2 V; I _{COM} = 100 mA | 3.0 4.3 | | 0.05 0.05 | | 0.05 0.05 | Ω |
| I _{NC(OFF)} I _{NO(OFF)} | NC or NO Off Leakage Current (Note 3) | V _{IN} = V _{IL} or V _{IH} V _{NO} or V _{NC} = 0.3 V V _{COM} = 4.0 V | 4.3 | -5.0 | 5.0 | -50 | 50 | nA |
| I _{COM(ON)} | COM ON Leakage Current (Note 3) | V _{IN} = V _{IL} or V _{IH} V _{NO} 0.3 V or 4.0 V with V _{NC} floating or V _{NC} 0.3 V or 4.0 V with V _{NO} floating V _{COM} = 0.3 V or 4.0 V | 4.3 | -10 | 10 | -100 | 100 | nA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.

4. Flatness is defined as the difference between the maximum and minimum value of On-resistance as measured over the specified analog signal ranges.

5. ΔR_{ON} = R_{ON(MAX)} - R_{ON(MIN)} between NC1 and NC2 or between NO1 and NO2.

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NLAS5223BL DC CHARACTERISTICS – DIGITAL SECTION (Voltages Referenced to GND)

| Symbol | Parameter | Condition | V _{CC} | Guaranteed Limit | | Unit |
|------------------|---|---|-----------------|------------------|----------------|------|
| | | | | 25°C | -40°C to +85°C | |
| V _{IH} | Minimum High-Level Input Voltage, Select Inputs | | 3.0 | 1.3 | 1.3 | V |
| | | | 4.3 | 1.6 | 1.6 | |
| V _{IL} | Maximum Low-Level Input Voltage, Select Inputs | | 3.0 | 0.5 | 0.5 | V |
| | | | 4.3 | 0.6 | 0.6 | |
| I _{IN} | Maximum Input Leakage Current, Select Inputs | V _{IN} = 4.5 V or GND | 4.3 | ±0.1 | ±1.0 | μA |
| I _{OFF} | Power Off Leakage Current | V _{IN} = 4.5 V or GND | 0 | ±0.5 | ±2.0 | μA |
| I _{CC} | Maximum Quiescent Supply Current (Note 6) | Select and V _{IS} = V _{CC} or GND | 1.65 to 4.5 | ±1.0 | ±2.0 | μA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.

NLAS5223BL DC ELECTRICAL CHARACTERISTICS – ANALOG SECTION

| Symbol | Parameter | Condition | V _{CC} | Guaranteed Maximum Limit | | | | Unit |
|--|--|--|-----------------|--------------------------|------|----------------|------|------|
| | | | | 25°C | | -40°C to +85°C | | |
| | | | | Min | Max | Min | Max | |
| R _{ON} | NC/NO On-Resistance (Note 7) | V _{IN} = V _{IL} or V _{IN} = V _{IH} V _{IS} = GND to V _{CC} I _{COM} = 100 mA | 3.0 | | 0.4 | | 0.5 | Ω |
| | | | 4.3 | | 0.35 | | 0.4 | |
| R _{FLAT} | NC/NO On-Resistance Flatness (Notes 7 and 8) | I _{COM} = 100 mA V _{IS} = 0 to V _{CC} | 3.0 | | 0.16 | | 0.20 | Ω |
| | | | 4.3 | | 0.11 | | 0.14 | |
| ΔR _{ON} | On-Resistance Match Between Channels (Notes 7 and 9) | V _{IS} = 1.5 V; I _{COM} = 100 mA V _{IS} = 2.2 V; I _{COM} = 100 mA | 3.0 | | 0.05 | | 0.05 | Ω |
| | | | 4.3 | | 0.05 | | 0.05 | |
| I _{NC(OFF)} I _{NO(OFF)} | NC or NO Off Leakage Current (Note 7) | V _{IN} = V _{IL} or V _{IH} V _{NO} or V _{NC} = 0.3 V V _{COM} = 4.0 V | 4.3 | -10 | 10 | -100 | 100 | nA |
| I _{COM(ON)} | COM ON Leakage Current (Note 7) | V _{IN} = V _{IL} or V _{IH} V _{NO} 0.3 V or 4.0 V with V _{NC} floating or V _{NC} 0.3 V or 4.0 V with V _{NO} floating V _{COM} = 0.3 V or 4.0 V | 4.3 | -10 | 10 | -100 | 100 | nA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.

8. Flatness is defined as the difference between the maximum and minimum value of On-resistance as measured over the specified analog signal ranges.

9. ΔR_{ON} = R_{ON(MAX)} – R_{ON(MIN)} between NC1 and NC2 or between NO1 and NO2.

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AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

| Symbol | Parameter | Test Conditions | V_{CC} (V) | V_{IS} (V) | Guaranteed Maximum Limit | | | | | Unit |
|-----------|--------------------------------|---|-----------------|-----------------|--------------------------|------|-----|----------------|-----|------|
| | | | | | 25°C | | | -40°C to +85°C | | |
| | | | | | Min | Typ* | Max | Min | Max | |
| t_{ON} | Turn-On Time | $R_L = 50 \Omega$, $C_L = 35$ pF (Figures 3 and 4) | 2.3 – 4.5 | 1.5 | | | 50 | | 60 | ns |
| t_{OFF} | Turn-Off Time | $R_L = 50 \Omega$, $C_L = 35$ pF (Figures 3 and 4) | 2.3 – 4.5 | 1.5 | | | 30 | | 40 | ns |
| t_{BBM} | Minimum Break-Before-Make Time | $V_{IS} = 3.0$ $R_L = 50 \Omega$, $C_L = 35$ pF (Figure 2) | 3.0 | 1.5 | 2 | 15 | | | | ns |

| | | Typical @ 25, $V_{CC} = 3.6$ V | |
|-------------|---|--------------------------------|--|
| C_{IN} | Control Pin Input Capacitance | 3.5 | |
| $C_{NO/NC}$ | NO, NC Port Capacitance | 60 | |
| C_{COM} | COM Port Capacitance When Switch is Enabled | 200 | |

*Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

| Symbol | Parameter | Condition | V_{CC} (V) | 25°C | Unit |
|-----------|--|---|-----------------|---------|------|
| | | | | Typical | |
| BW | Maximum On-Channel -3 dB Bandwidth or Minimum Frequency Response | V_{IN} centered between V_{CC} and GND (Figure 5) | 1.65 – 4.5 | 19 | MHz |
| V_{ONL} | Maximum Feed-through On Loss | $V_{IN} = 0$ dBm @ 100 kHz to 50 MHz V_{IN} centered between V_{CC} and GND (Figure 5) | 1.65 – 4.5 | -0.06 | dB |
| V_{ISO} | Off-Channel Isolation | $f = 100$ kHz; $V_{IS} = 1$ V RMS; $C_L = 5.0$ pF V_{IN} centered between V_{CC} and GND (Figure 5) | 1.65 – 4.5 | -68 | dB |
| Q | Charge Injection Select Input to Common I/O | $V_{IN} = V_{CC}$ to GND, $R_{IS} = 0 \Omega$, $C_L = 1.0$ nF $Q = C_L \times DV_{OUT}$ (Figure 6) | 1.65 – 4.5 | 38 | pC |
| THD | Total Harmonic Distortion THD + Noise | $F_{IS} = 20$ Hz to 20 kHz, $R_L = R_{gen} = 600 \Omega$, $C_L = 50$ pF $V_{IS} = 2.0$ V RMS | 3.0 | 0.08 | % |
| VCT | Channel-to-Channel Crosstalk | $f = 100$ kHz; $V_{IS} = 1.0$ V RMS, $C_L = 5.0$ pF, $R_L = 50 \Omega$ V_{IN} centered between V_{CC} and GND (Figure 5) | 1.65 – 4.5 | -70 | dB |

10. Off-Channel Isolation = $20 \log_{10} (V_{COM}/V_{NO})$, V_{COM} = output, V_{NO} = input to off switch.

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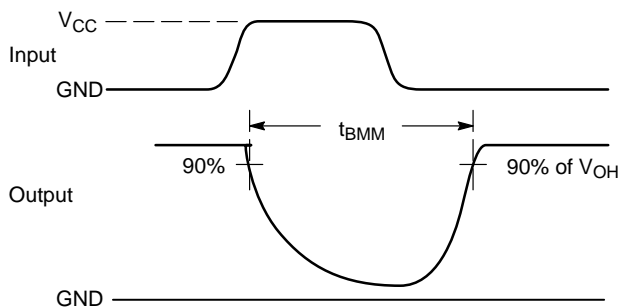
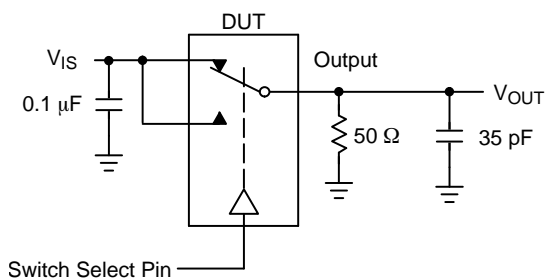


Figure 2. t_{BMM} (Time Break-Before-Make)

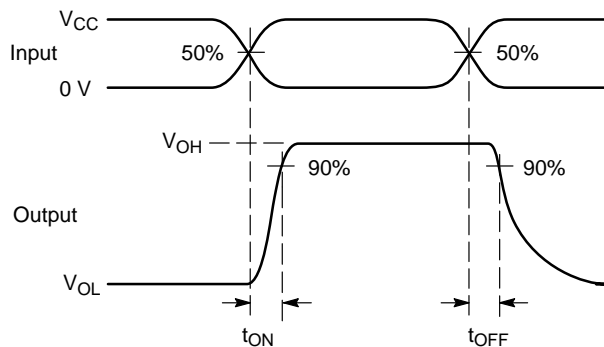
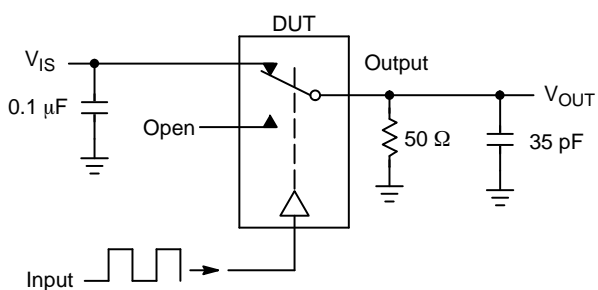


Figure 3. t_{ON}/t_{OFF}

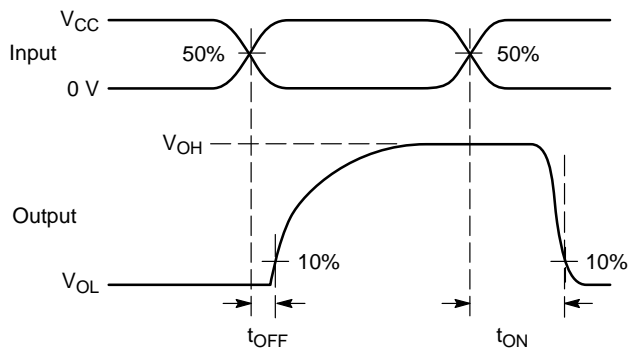
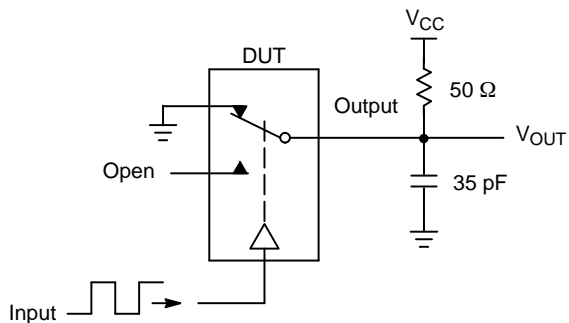
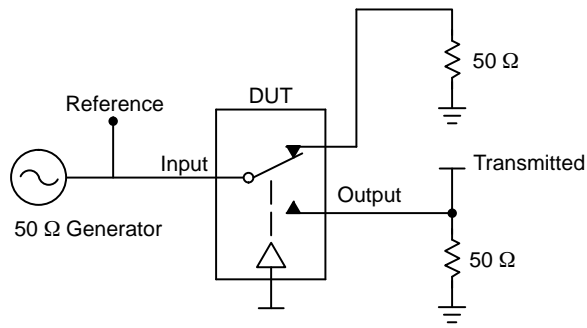


Figure 4. t_{ON}/t_{OFF}

NLAS5223B, NLAS5223BL



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz}$$

$$V_{ONL} = \text{On Channel Loss} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 5. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/ V_{ONL}

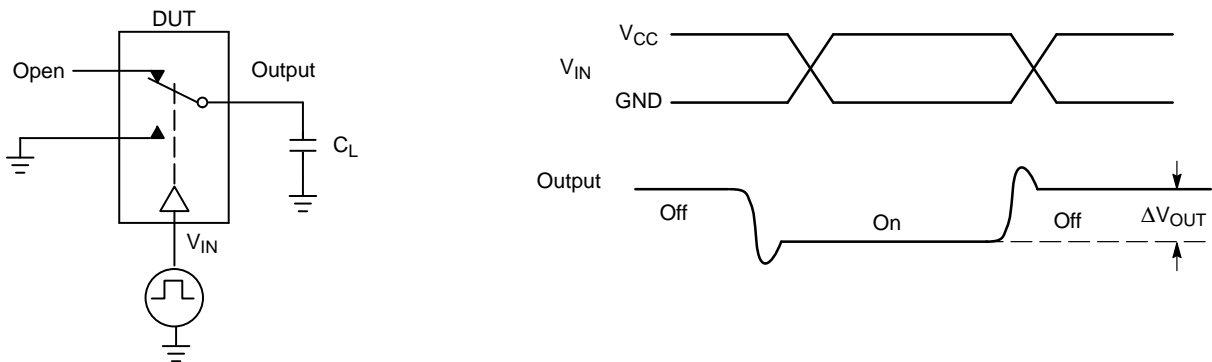


Figure 6. Charge Injection: (Q)

NLAS5223B, NLAS5223BL

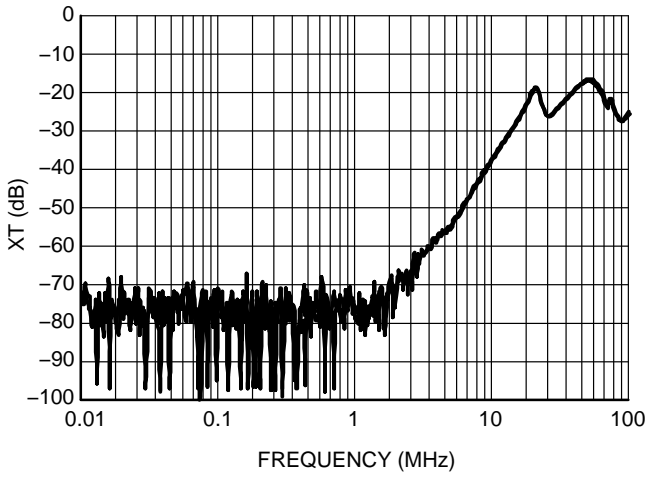


Figure 7. Cross Talk vs. Frequency
@ $V_{CC} = 4.3 \text{ V}$

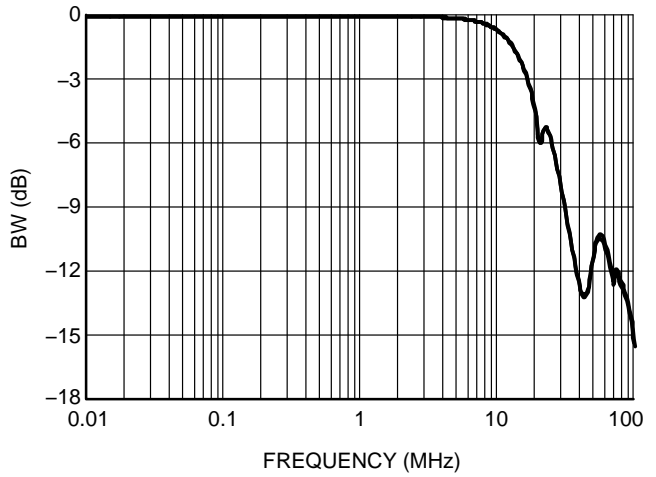


Figure 8. Bandwidth vs. Frequency

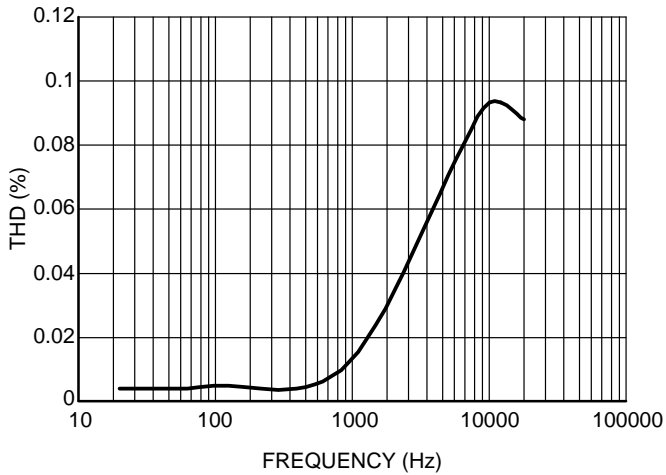


Figure 9. Total Harmonic Distortion

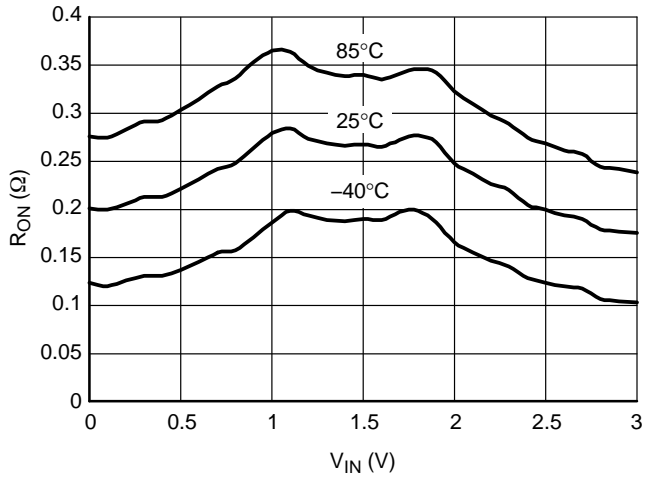


Figure 10. On-Resistance vs. Input Voltage
@ $V_{CC} = 3.0 \text{ V}$

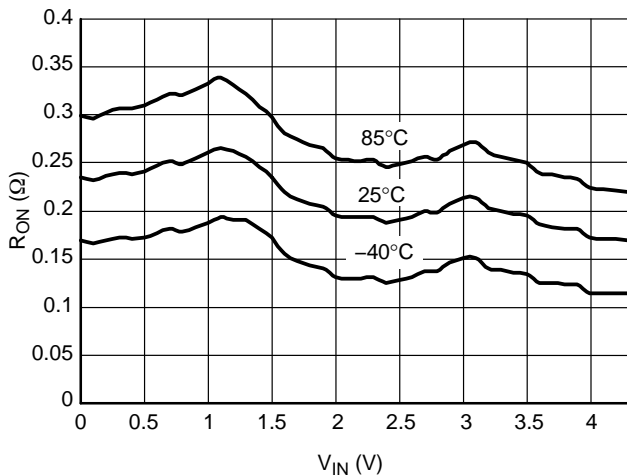


Figure 11. On-Resistance vs. Input Voltage
@ $V_{CC} = 4.3 \text{ V}$

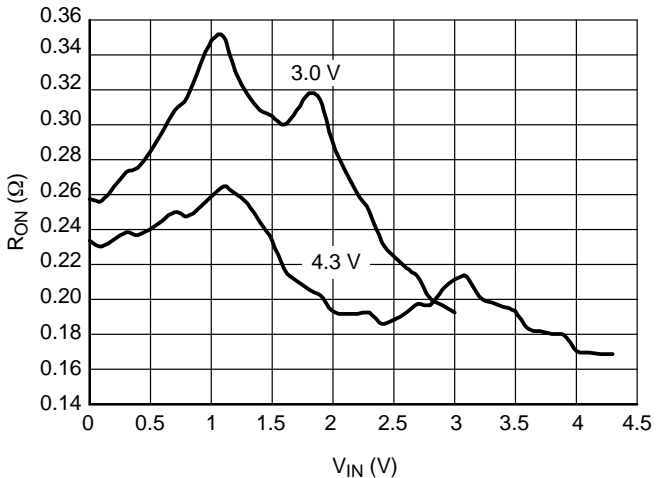


Figure 12. On-Resistance vs. Input Voltage

NLAS5223B, NLAS5223BL

ORDERING INFORMATION

| Device | Package | Shipping† |
|-----------------|---------------------|--------------------|
| NLAS5223BMNR2G | WQFN10 (Pb-Free) | 3000 / Tape & Reel |
| NLAS5223BLMNR2G | WQFN10 (Pb-Free) | 3000 / Tape & Reel |
| NLAS5223BMUR2G | UQFN10 (Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

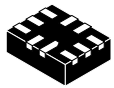
PACKAGE DIMENSIONS

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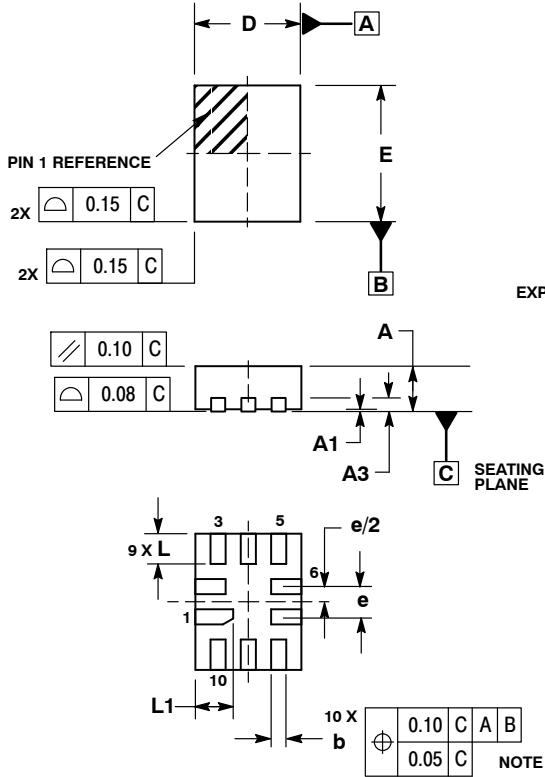


WQFN10, 1.4x1.8, 0.4P
CASE 488AQ-01
ISSUE C

DATE 19 JUN 2007



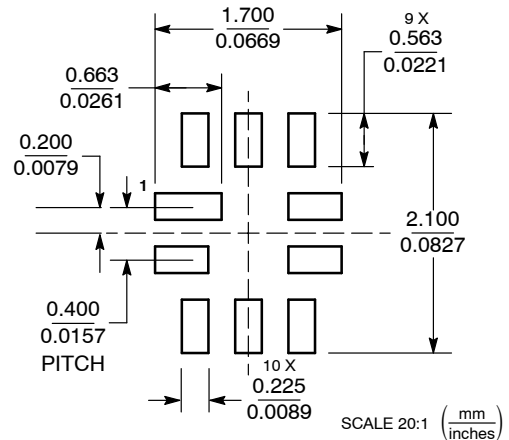
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- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
 5. EXPOSED PADS CONNECTED TO DIE FLAG. USED AS TEST CONTACTS.

| MILLIMETERS | | |
|-------------|------|-------|
| DIM | MIN | MAX |
| A | 0.70 | 0.80 |
| A1 | 0.00 | 0.050 |
| A3 | 0.20 | REF |
| b | 0.15 | 0.25 |
| D | 1.40 | BSC |
| E | 1.80 | BSC |
| e | 0.40 | BSC |
| L | 0.30 | 0.50 |
| L1 | 0.40 | 0.60 |
| M1 | 0.00 | 0.05 |

MOUNTING FOOTPRINT



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| DOCUMENT NUMBER: | 98AON20791D | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| DESCRIPTION: | WQFN10, 1.4 X 1.8, 0.4P | PAGE 1 OF 1 |

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MECHANICAL CASE OUTLINE

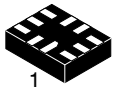
PACKAGE DIMENSIONS

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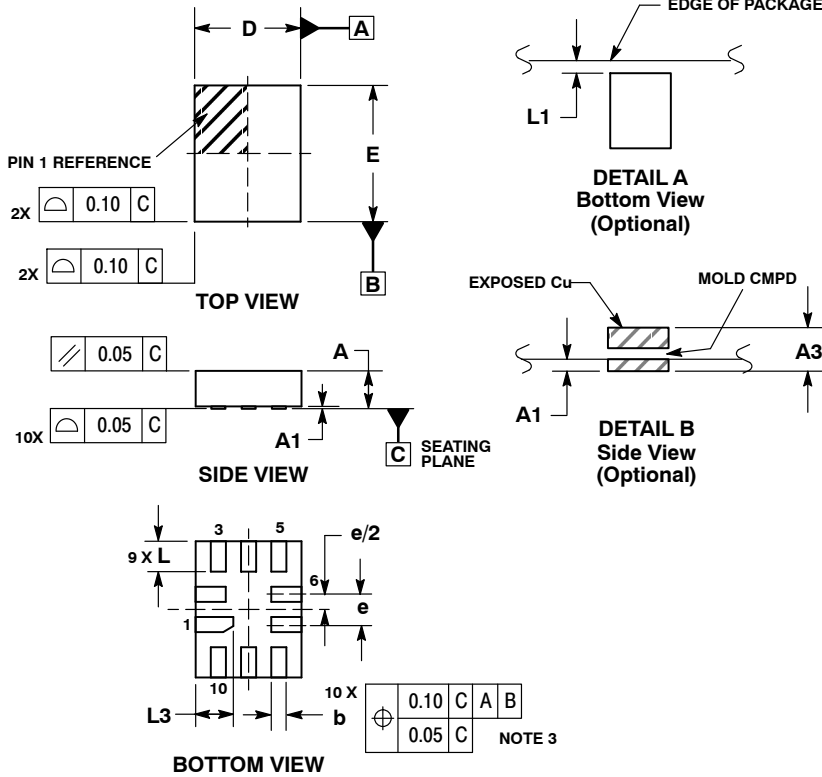


UQFN10 1.4x1.8, 0.4P CASE 488AT-01 ISSUE A

DATE 01 AUG 2007



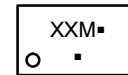
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NOTES:

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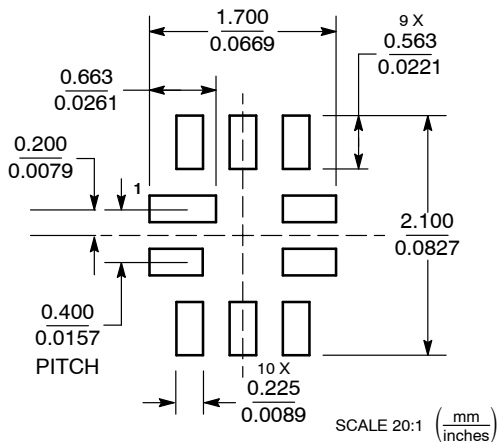
GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
 - M = Date Code
 - = Pb-Free Package
- (Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

MOUNTING FOOTPRINT



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| DESCRIPTION: | 10 PIN UQFN, 1.4 X 1.8, 0.4P | PAGE 1 OF 1 |

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